

Standard Rectifier Module

$$V_{RRM} = 2 \times 1200 \text{ V}$$

$$I_{FAV} = 310 \text{ A}$$

$$V_F = 1,03 \text{ V}$$

Phase leg

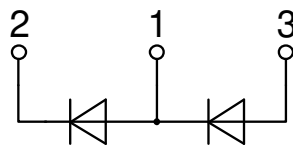
Part number

MDD312-12N1



Backside: isolated

 E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For single and three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: Y1

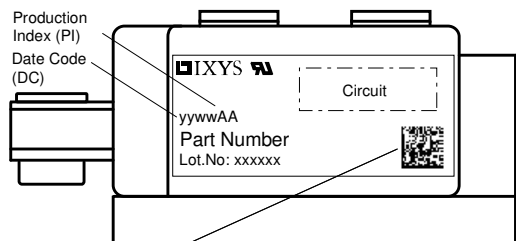
- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Base plate: Copper internally DCB isolated
- Advanced power cycling

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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1300	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1200	V
I_R	reverse current	$V_R = 1200\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			500	μA
		$V_R = 1200\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			30	mA
V_F	forward voltage drop	$I_F = 300\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1,13	V
		$I_F = 600\text{ A}$				1,33	V
		$I_F = 300\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			1,03	V
		$I_F = 600\text{ A}$				1,29	V
I_{FAV}	average forward current	$T_C = 100^{\circ}\text{C}$	$T_{VJ} = 150^{\circ}\text{C}$			310	A
$I_{F(RMS)}$	RMS forward current	180° sine $d = 0.5$				520	A
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 150^{\circ}\text{C}$		0,80	V
r_F	slope resistance					0,6	mΩ
R_{thJC}	thermal resistance junction to case					0,12	K/W
R_{thCH}	thermal resistance case to heatsink				0,04		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				1040	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms; (50 Hz), sine}$	$T_{VJ} = 45^{\circ}\text{C}$			10,8	kA
		$t = 8,3\text{ ms; (60 Hz), sine}$	$V_R = 0\text{ V}$			11,7	kA
		$t = 10\text{ ms; (50 Hz), sine}$	$T_{VJ} = 150^{\circ}\text{C}$			9,18	kA
		$t = 8,3\text{ ms; (60 Hz), sine}$	$V_R = 0\text{ V}$			9,92	kA
I^2t	value for fusing	$t = 10\text{ ms; (50 Hz), sine}$	$T_{VJ} = 45^{\circ}\text{C}$			583,2	kA^2s
		$t = 8,3\text{ ms; (60 Hz), sine}$	$V_R = 0\text{ V}$			566,1	kA^2s
		$t = 10\text{ ms; (50 Hz), sine}$	$T_{VJ} = 150^{\circ}\text{C}$			421,4	kA^2s
		$t = 8,3\text{ ms; (60 Hz), sine}$	$V_R = 0\text{ V}$			409,0	kA^2s
C_J	junction capacitance	$V_R = 400\text{ V; } f = 1\text{ MHz}$		$T_{VJ} = 25^{\circ}\text{C}$	381		pF

Package Y1				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal				600	A
T _{VJ}	virtual junction temperature			-40		150	°C
T _{op}	operation temperature			-40		125	°C
T _{stg}	storage temperature			-40		125	°C
Weight					680		g
M _D	mounting torque			4,5		7	Nm
M _T	terminal torque			11		13	Nm
d _{Spp/App}	creepage distance on surface striking distance through air	terminal to terminal		16,0			mm
d _{Spb/Apb}		terminal to backside		16,0			mm
V _{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA	4800			V
		t = 1 minute		4000			V

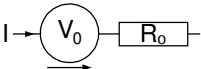


Data Matrix: *part no.* (1-19), *DC + PI* (20-25), *lot.no.#* (26-31), *blank* (32), *serial no.#* (33-36)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDD312-12N1	MDD312-12N1	Box	3	463426

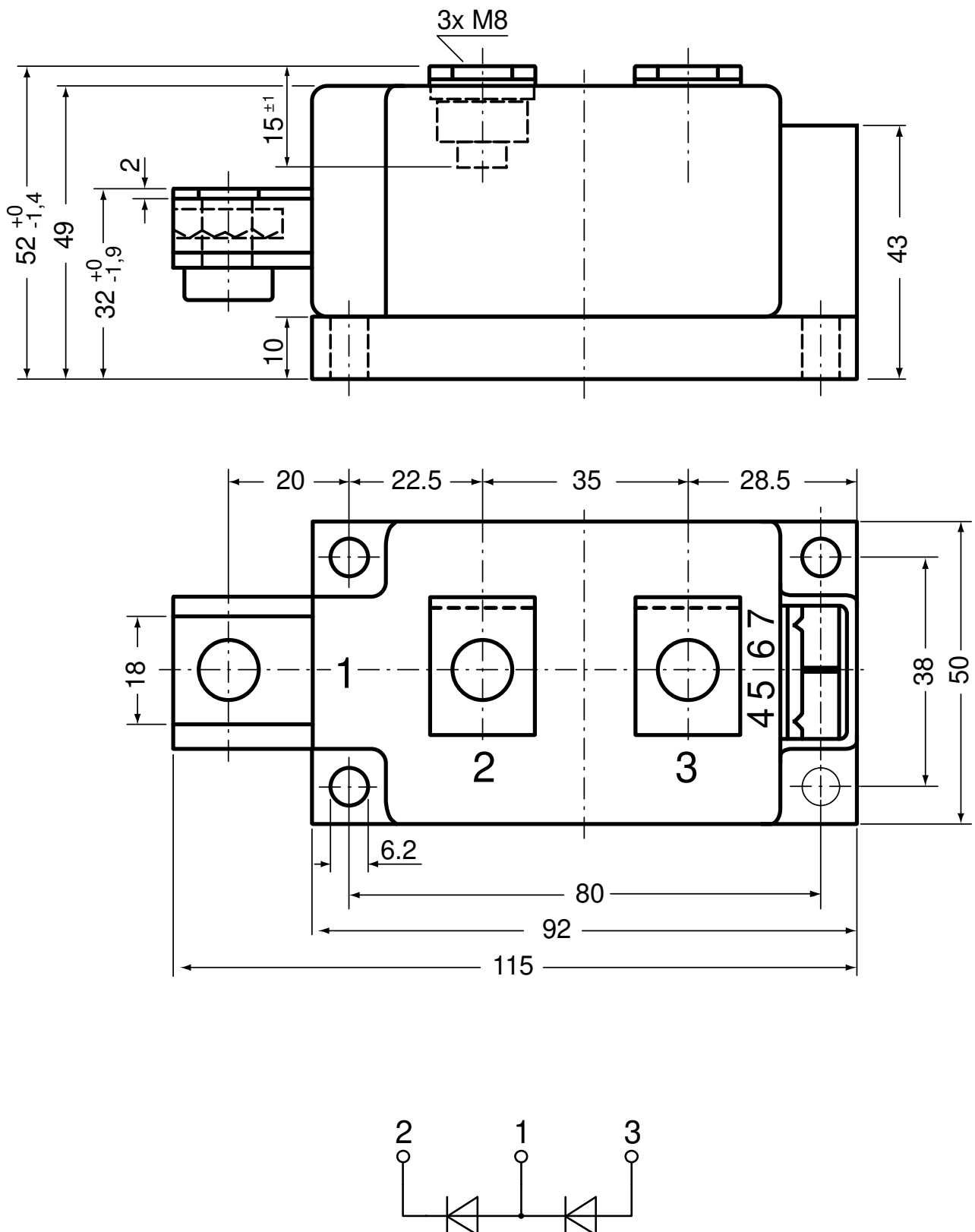
Similar Part	Package	Voltage class
MDD312-14N1	Y1-CU	1400
MDD312-16N1	Y1-CU	1600
MDD312-18N1	Y1-CU	1800
MDD312-20N1	Y1-CU	2000

MDD312-22N1	Y1-CU	2200
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Equivalent Circuits for Simulation			* on die level	$T_{VJ} = 150^{\circ}\text{C}$
		Rectifier		
$V_{0\text{ max}}$	threshold voltage	0,8		V
$R_{0\text{ max}}$	slope resistance *	0,4		mΩ



Outlines Y1



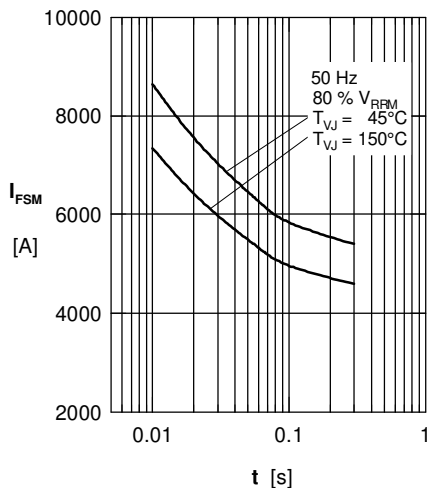
Rectifier


Fig. 1 Surge overload current
 I_{FSM} : Crest value, t : duration

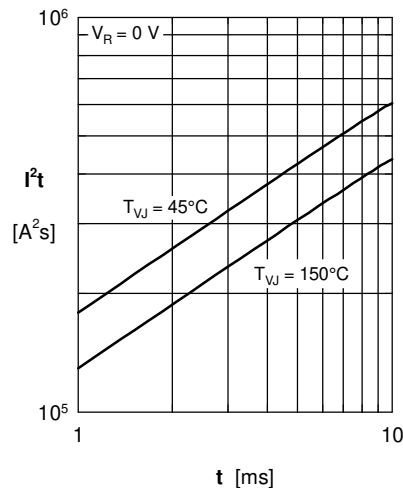


Fig. 2 I^2t versus time (1-10 ms)

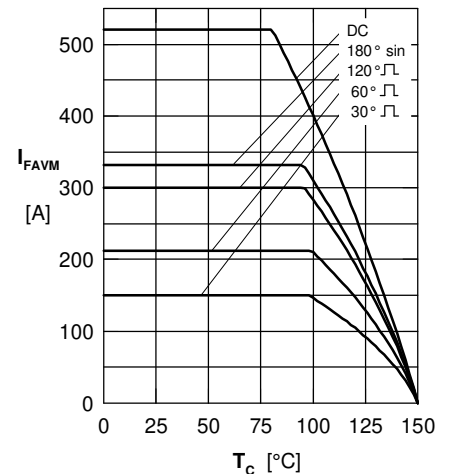


Fig. 3 Maximum forward current at case temperature

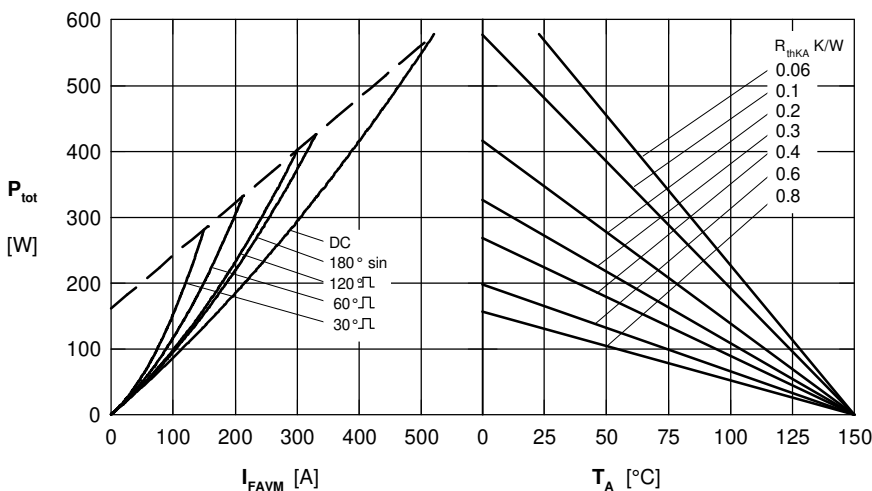


Fig. 4 Power dissipation vs. forward current & ambient temperature (per diode)

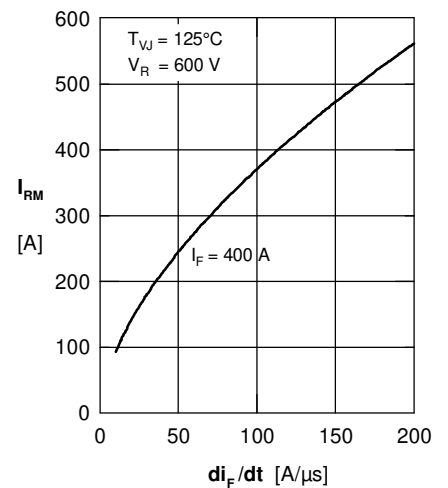


Fig. 5 Typ. peak reverse current

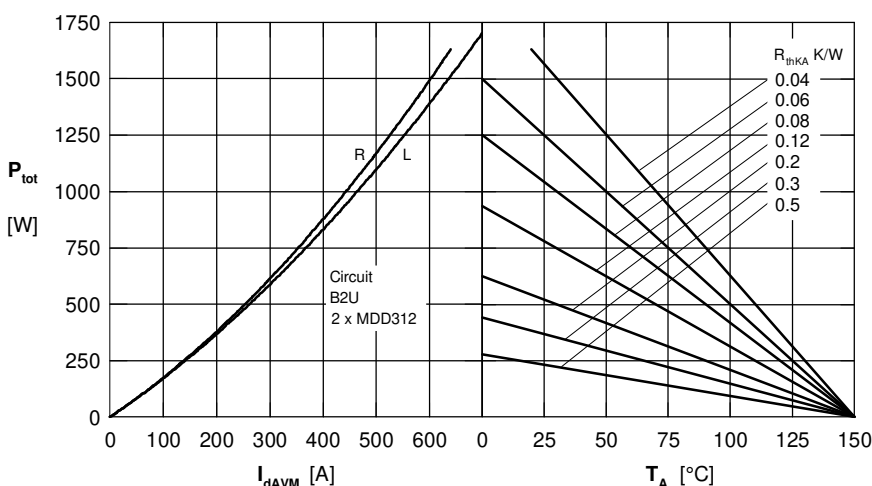


Fig. 6 Single phase rectifier bridge: Power dissipation vs. direct output current and ambient temperature R = resistive load, L = inductive load

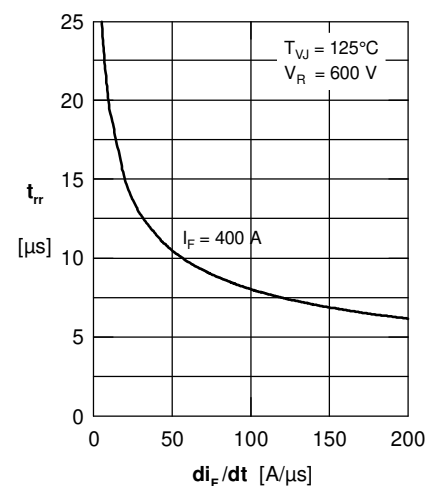


Fig. 7 Typ. recovery time t_{rr} versus $-di_F/dt$

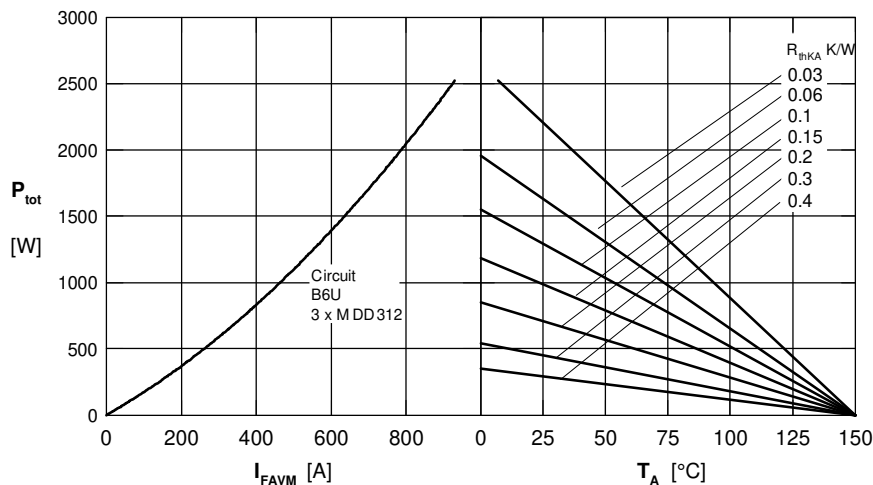
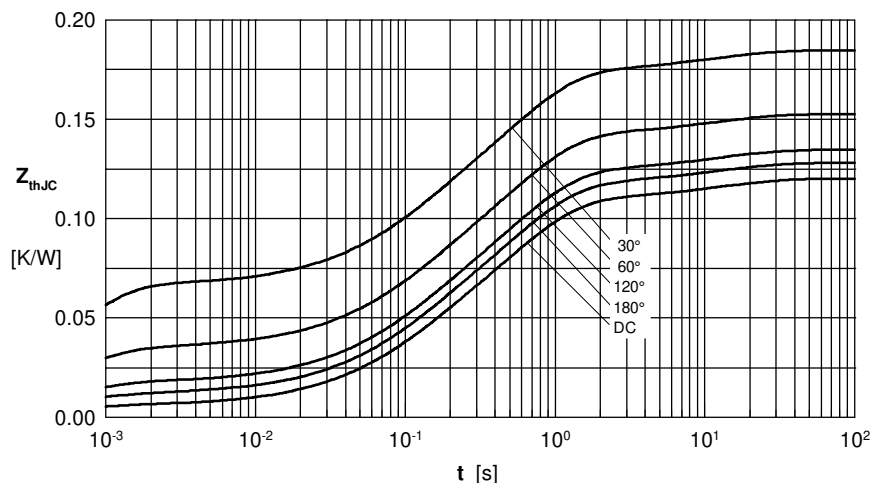
Rectifier


Fig. 8 Three phase rectifier bridge: Power dissipation vs. direct output current & ambient temperature



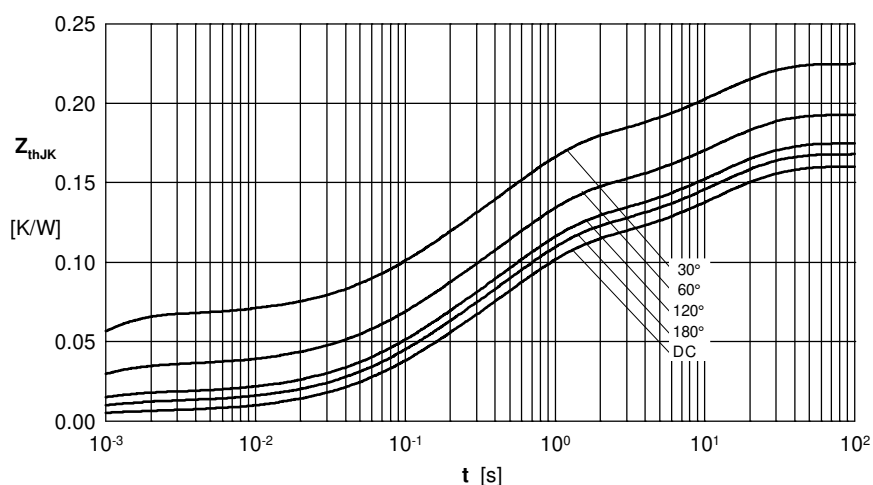
R_{thJC} for various conduction angles d :

d	R_{thJC} [K/W]
DC	0.120
180°	0.128
120°	0.135
60°	0.153
30°	0.185

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0058	0.00054
2	0.0310	0.09800
3	0.0720	0.54000
4	0.0112	12.0000

Fig. 9 Transient thermal impedance junction to case (per diode)



R_{thJK} for various conduction angles d :

d	R_{thJK} [K/W]
DC	0.160
180°	0.168
120°	0.175
60°	0.193
30°	0.225

Constants for Z_{thJK} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0058	0.00054
2	0.0310	0.09800
3	0.0720	0.54000
4	0.0112	12.0000
5	0.0400	12.0000

Fig. 10 Transient thermal impedance junction to heatsink (per diode)